

CVD Diamond Pixel Detectors

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for The RD42 Collaboration

- CVD diamond as a detector material
- Pixel detector development efforts
- Recent test results

CVD Diamond as a Detector Material

property	diamond	silicon
band gap (eV)	5.5	1.12
energy to create e-h pair (eV)	13	3.6
breakdown field (V/cm)	10^7	3×10^5
resistivity (Ω/cm)	10^{11}	2.3×10^5
electron mobility ($\text{cm}^{-2}\text{V}^{-1}\text{s}^{-1}$)	1800	1350
hole mobility ($\text{cm}^{-2}\text{V}^{-1}\text{s}^{-1}$)	1200	480
signal created by MIP. ($\text{e}/\mu\text{m}$)	36	89
cohesive energy (eV/atom)	7.37	4.63
mass density (gcm^{-1})	3.5	2.33
dielectric constant	5.7	11.9
radiation length (cm)	12.0	9.4
thermal expansion coefficient	8.0×10^{-7}	2.6×10^{-6}
thermal conductivity ($\text{W m}^{-1} \text{K}^{-1}$)	1000-2000	150

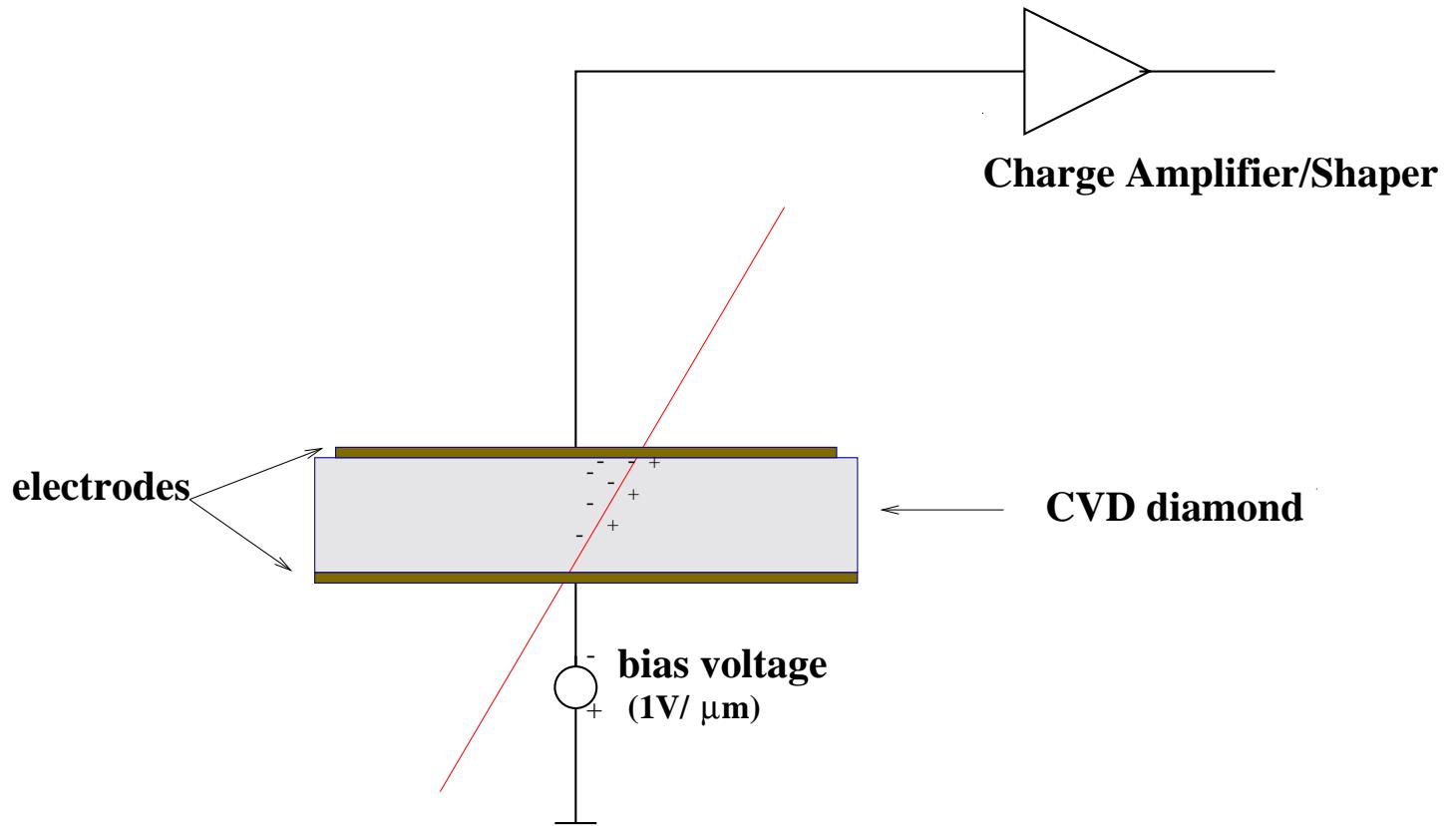
Advantages:

- Large mobility: fast signal
- Good thermal conductivity: better cooling
- Low dielectric constant: low noise
- High resistivity: low leakage current
- Radiation tolerant

Disadvantages

- Smaller signal ($\approx \frac{1}{3}$ of Si)
- Polycrystalline (non-uniform)
- Relatively new material:
only one manufacturer (De Beers) produces
highest quality CVD diamond

Principle of Operation:

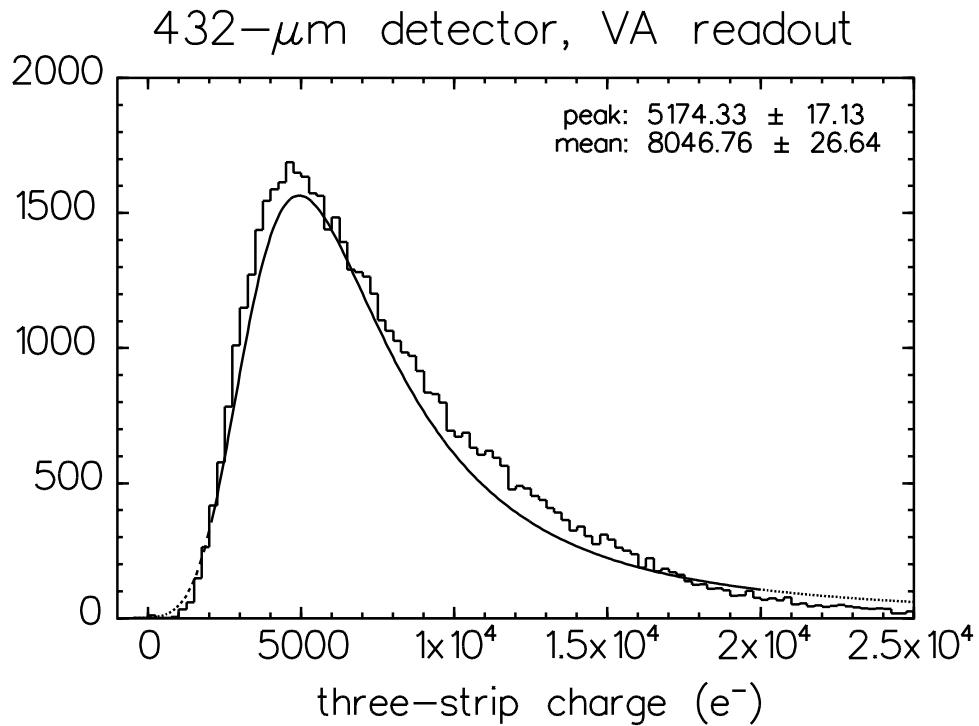


36 e-h pairs per micron for MIP.

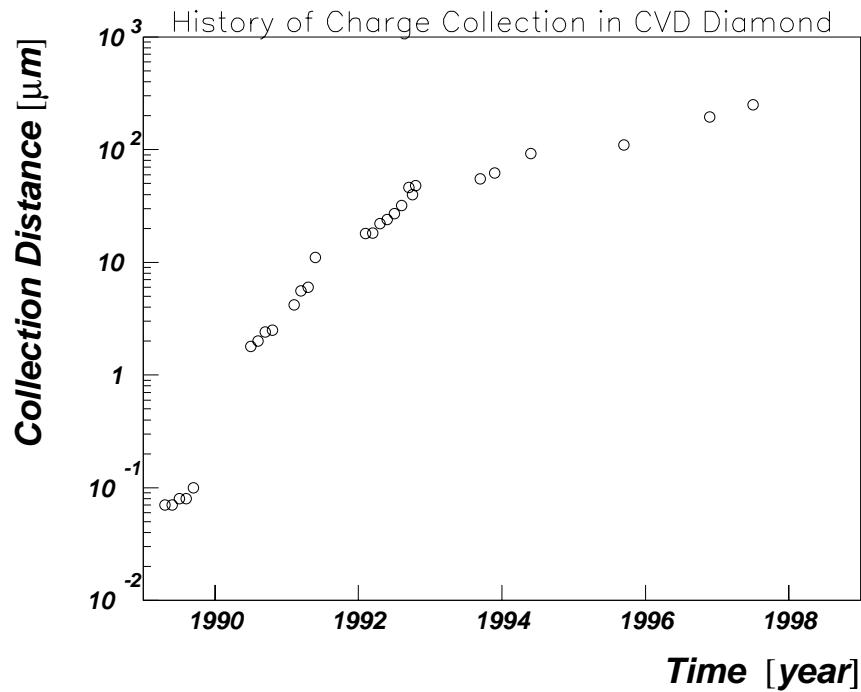
Signal is limited by the collection distance

Simple fabrication technique.

Diamond is reusable

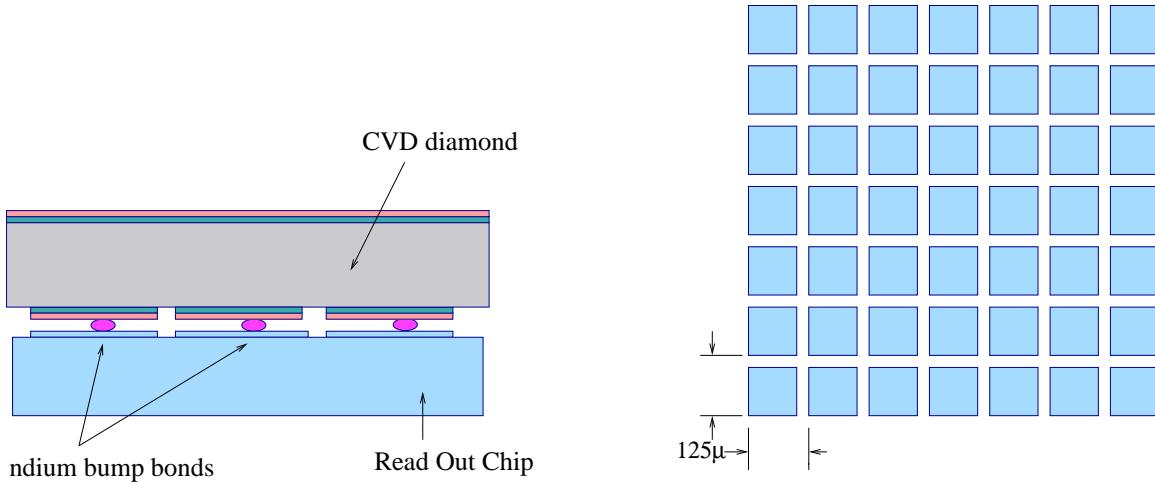


Signal distribution from a CVD diamond detector



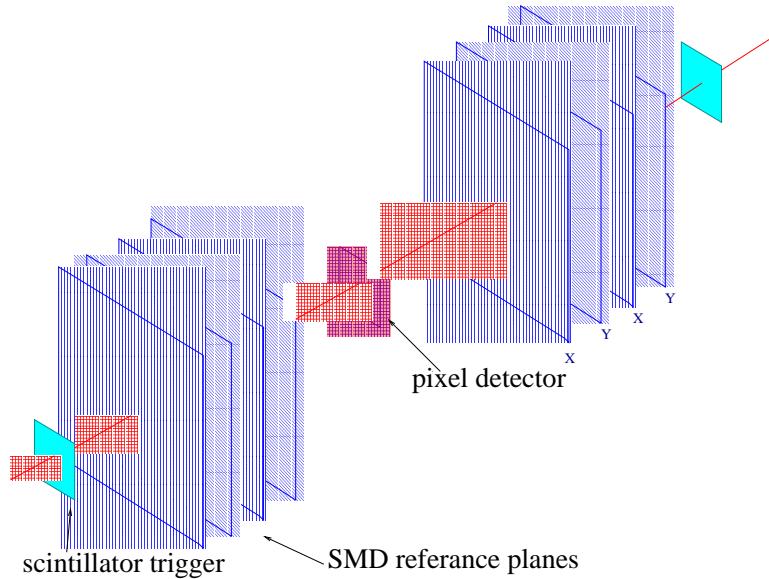
Collection distance has improved significantly

CVD Diamond Pixel Detectors



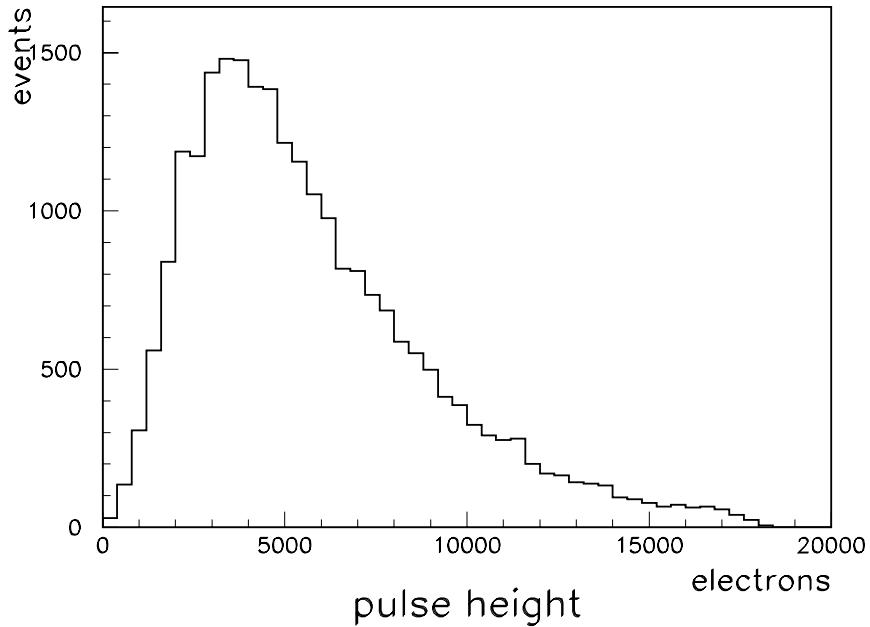
- $125 \times 125\mu\text{m}$ pixels (W/Ti)
- Indium bump bonded to prototype CMS pixel readout chip
 - PS130 (Honeywell version)
 - pitch $125 \times 125\mu\text{m}$
 - active area 22 columns \times 32 rows
 - adjustable threshold for each pixel

First Beam Test Jan. 3-14 at Fermilab test beam



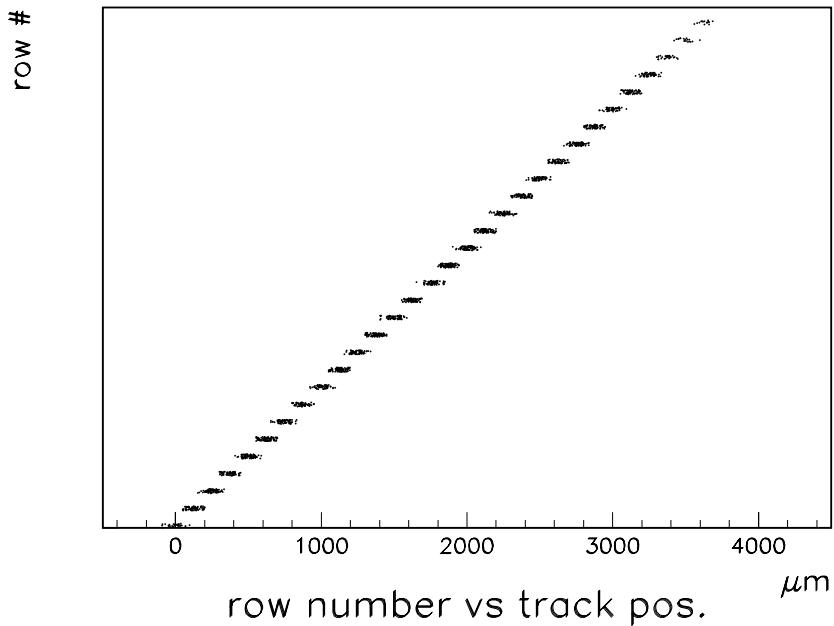
- Rutgers tracking telescope:
 - 8 SMD reference planes
 - better than $7\mu\text{m}$ extrapolation accuracy
 - scintillator (fiber) trigger
 - data rate 150 Hz
- Pixel detector:
 - active area 12 columns \times 30 rows (half of chip)
 - pixel thresholds at ≈ 2000 e
 - pixel threshold rms spread ≈ 600 e
 - Noise: 750 e (common mode 500 e)
- Data collected: > 100 hits/pixel

Test Beam Results



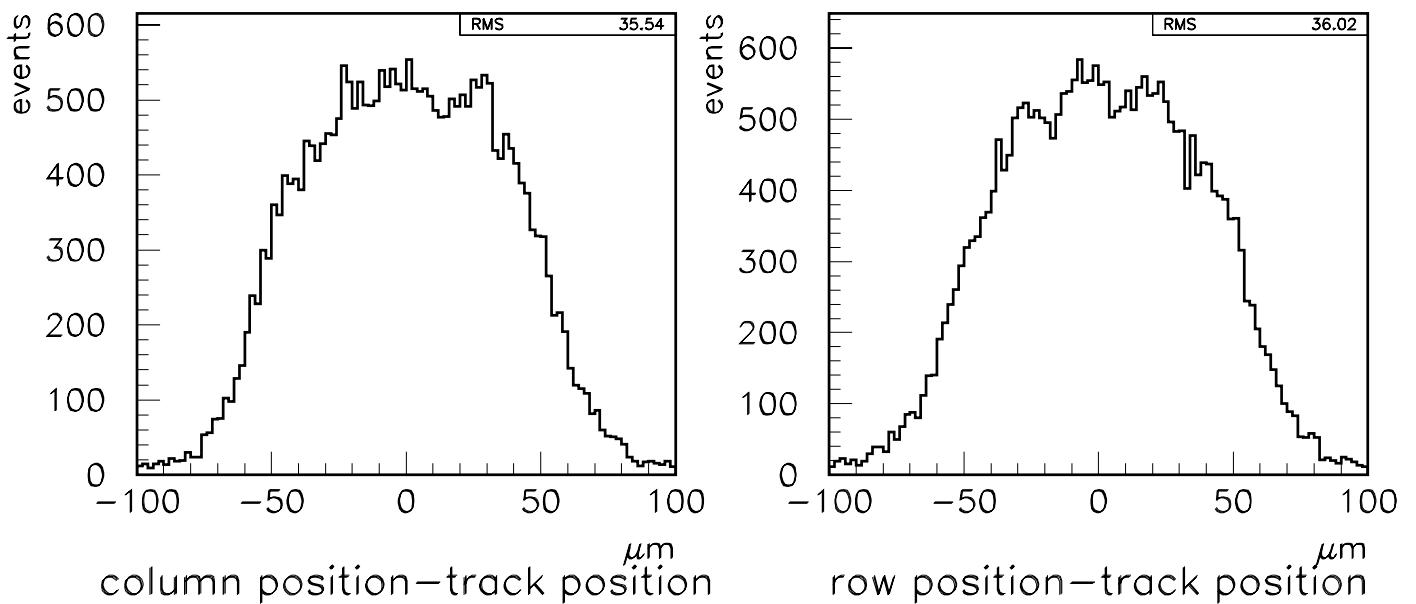
Diamond pixel signal:

- Lower slope may be affected by thresholds/noise



Good track and pixel hit correlation

Position Resolution of Diamond Pixel Detector

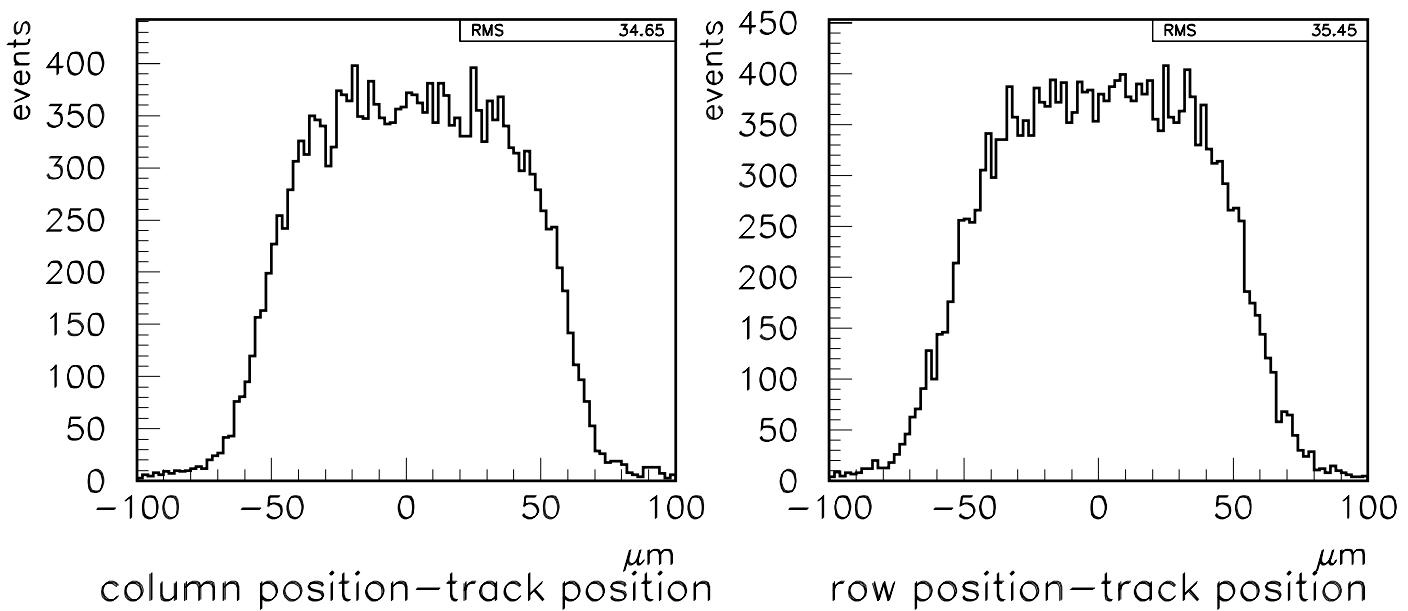


digital resolution:

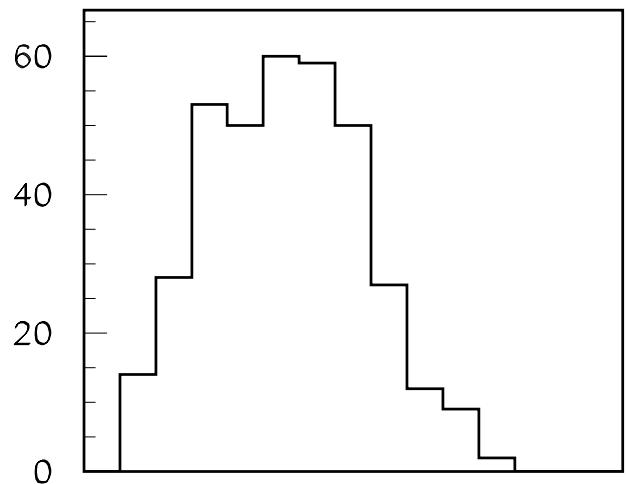
$$125\mu\text{m}/\sqrt{12} = 36\mu\text{m}$$

Similar to silicon

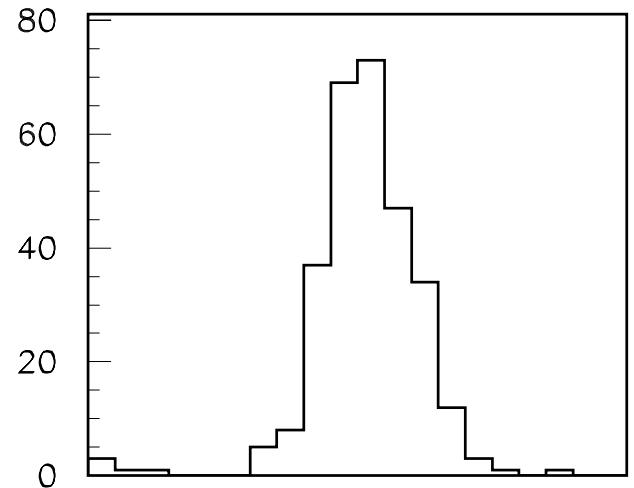
Position Resolution of Silicon Pixel Detector



Pixel Efficiency



Diamond pixel efficiency

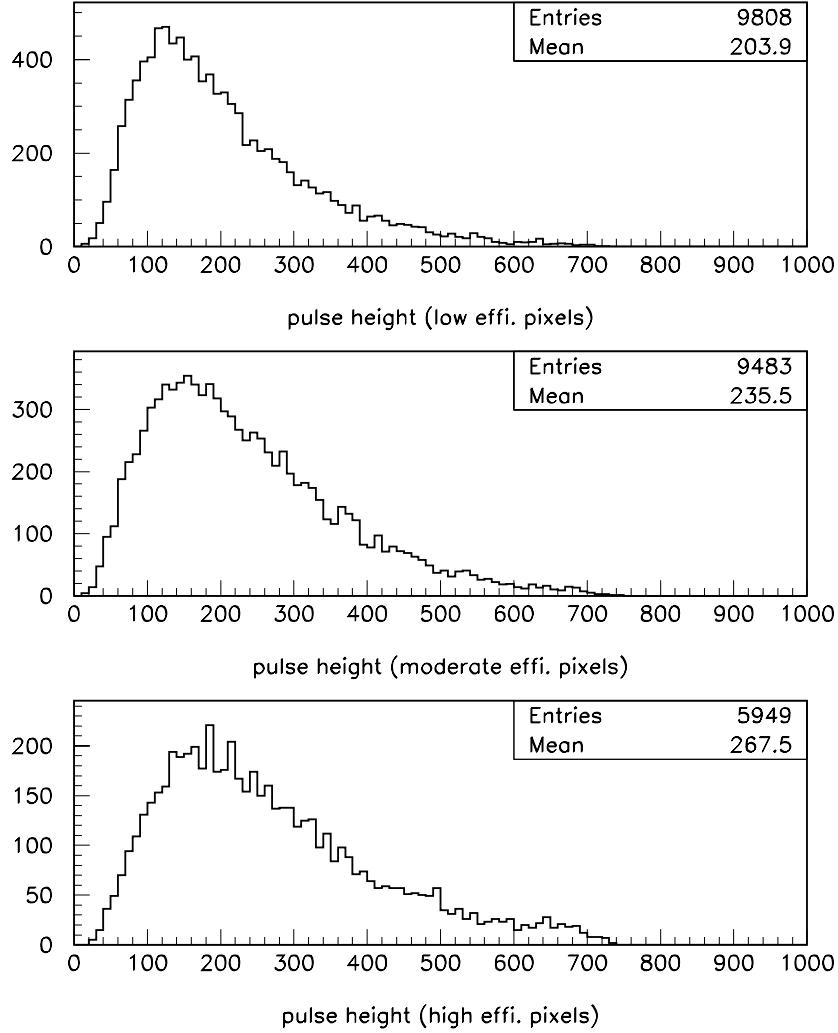


Si pixel efficiency

NOTE: Efficiencies are not normalized

Diamond efficiency spread larger than of Si.

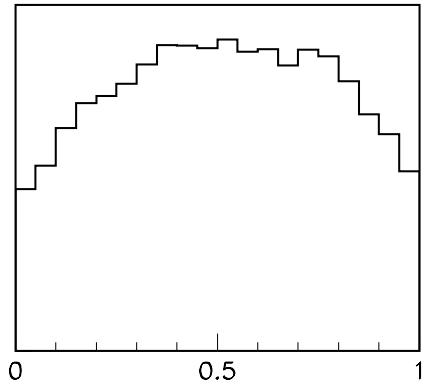
Efficiency and Signal level.



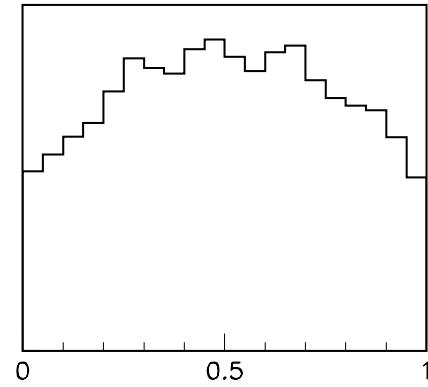
Variation in efficiency:

- consistent with the variation of signal level
 - non uniformity of signal from diamond
 - threshold/gain/contact variations
 - charge spread in diamond

Efficiency and hit position



Efficiency vs position in column



Efficiency vs position in row

Efficiency is lower near pixel boundaries

⇒ charge spreading.

- Current results are from a preliminary run
- Number of beam tests are planned:
 - CERN X7 beam line
taking data now
 - CERN X5 beam line
June/July - proton irradiation in between
 - CERN H2 beam line
August - in a 3 Tesla magnetic field

Goals of Future Beam Tests.

- Use improved sensor material
- Higher statistics (>1000 hits/pixel)
- Tune/reduce ROC threshold (reduce threshold spread)
- Reduce noise
- Measure resolution with sensor rotated wrt beam
(with charge sharing)
- Measure resolution with Lorentz drift in 3 Tesla field
- Study radiation damage ($10^{15}/\text{cm}^2$ particle fluance)

All with side-by-side comparision with silicon.

